CBM2096

USB 2.0 Flash Disk Controller

Datasheet

Rev 1.0

Shenzhen Chipsbank Technologies Co.,Ltd.
7/F,Building No.12,Keji Central Road 2,
Software Park, High-Tech Industrial Park, Shenzhen,
P.R.China 518057
Tel: 0755-86169650-808
Fax: 0755-86169690
Email: info@chipsbank.com
URL: http://www.chipsbank.com

Revision History

Date	Rev No	Description
2011-02-24	1.0	Initial release

Contents

1 DESCRIPTION **4**

2 FEATURES **4**

3 BLOCK DIAGRAM **6**

4 PIN ASSIGNMENT **7**

4.1 TQFP48 (TOP SIDE) 7

5 PIN DESCRIPTION **8**

6 ELECTRICAL CHARACTERISTICS **11**

6.1 ABSOLUTE MAXIMUM RATINGS 11
6.2 RECOMMENDED OPERATING CONDITIONS 11
6.3 STATIC CHARACTERISTICS 12
6.4 DYNAMIC CHARACTERISTICS 12
6.4.1 Normal NAND FLASH Dynamic characteristics 12
6.4.2 ONFI NAND FLASH Dynamic characteristics 14
6.4.3 TOGGLE NAND FLASH Dynamic characteristics 19

7 MECHANICAL DIMENSIONS **24**

7.1 48-PIN CBM2096 PACKAGE OUTLINE DIMENSION 24

8 COPYRIGHT NOTICE **25**

1 Description

Fastest & Securest USB 2.0 Flash Disk Controller with dedicated 32-bit microprocessor

The CBM2096 is the USB 2.0 Flash Disk controller with the fastest transfer speed on the market. CBM2096 can reach theoretical flash access speed limit of over 32MByte/s for read and 20MByte/s for write.

The on-the-fly ECC engine is capable of correcting up to 16/25/29/30bits per 1024 bytes page . For data security, CBM2096 is designed with both hardware and software data protection technology to prevent data corruption even if it is powered off or unplugged during data transfer.

The CBM2096 supports all 8 /16 bit BUS wide async NAND flash memory available in the market. New flash can be supported by software re-configuration.

The CBM2096 supports all 8 bit BUS wide ONFI/TOGGLE NAND flash memory available in the market. New flash can be supported by software re-configuration.

The CBM2096 has both a) 5V to 3.3V LDO and b) power on reset circuits integrated. Thus greatly reduced BOM cost and eased layout burden.

The CBM2096 can work properly with ***no external crystal***. It was popularly used for UDP products.

The CBM2096 runs smoothly with all available hosts and PC platforms. Complied with USB specification rev. 2.0, the CBM2096 can be supported without additional driver under Win XP, Win 2000, Windows Me, Mac OS and Linux OS. With device driver installed, it can support Win 98/98SE as well. Comprehensive applications, such as PC boot up, disk partitions, password check for security disk, are available as part of our standard mass production software package.

The CBM2096 is available in 48-pin TQFP and 64-pin LQFP package, which are thinnest and smallest on the market. The 48-pin CBM2096 and the 64-pin CBM2096 all support up to 8 flash chips. Customers can choose different packages to meet their design requirement.

2 Features

- **USB Interface**

  High-speed USB 2.0 interface;

- **Fastest data transfer rate on the market**

  Single-channel mode(16bit): 32MB/s for Read, 20MB/s for Write
  Single-channel mode(8bit): 26MB/s for Read, 20MB/s for Write
  Fastest file copy rate on the market.

- **On-the-fly ECC built-in Hardware enhances reliability**

  ECC for NAND flash: 16/25/29/30 bit per page (1 page = 1024 bytes)

- **Special wear leveling algorithm to improve the flash life-time**

- **Hardware & Software Data Protection Technology**

  Prevent data corruption even if it is powered off or unplugged during data transfer.

- **SLC & MLC & TLC NAND Flash Interface**

  Support 8-bit and 16-bit Samsung SLC&MLC&TLC NAND flash.
  Support 8-bit and 16-bit Toshiba SLC&MLC&TLC NAND flash.
  Support 8-bit and 16-bit Hynix SLC&MLC&TLC NAND flash.
  Support 8-bit and 16-bit Sandisk SLC&MLC&TLC NAND flash.
  Support 8-bit and 16-bit Micron/Intel SLC&MLC&TLC NAND flash.
  Support 8-bit and 16-bit ST/Numony SLC&MLC NAND flash.
  Support 8-bit and 16-bit Infineon SLC&MLC NAND flash.
  Support PowerChip SLC&MLC Nand flash
  Support Spansion 3.3V MirrorBit-Quad flash
  Support Actrans Nand Flash
  Support ONFI2.0 DDR mode flash
  Support Samsung Toggle mode flash
  Software configuration to support various new flash memories
  Supports up to 8 flash chips

- **Proprietary 32-bit CISC microprocessor feature**

  Proprietary 32-bit CISC processor for USB protocol processing and flash access.

  Single cycle instruction period

- **Integrated 5v to 3.3v voltage regulator**
- **Disk partitions and password check for security disk available**
- **PC boot up as USB Zip Disk, USB Hard Disk or USB CDROM**
- **Auto run function**
- **Low power dissipation**

  Operating current 60mA (Bus power compatible)

- **Build-in LDO**

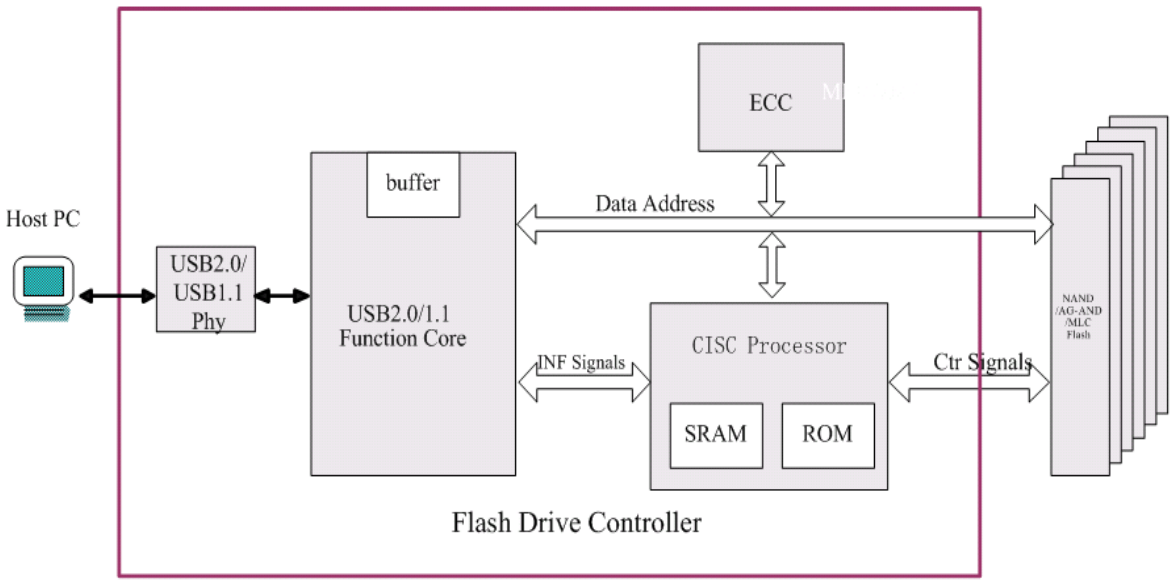
  Output maximum current up to 300mA

- **Build-in crystal**
- **Leading 0.16um CMOS technology**
- **48-pin TQFP /64-pin LQFP package**

  48-pin CBM2096 supports up to 8 Flash Chips

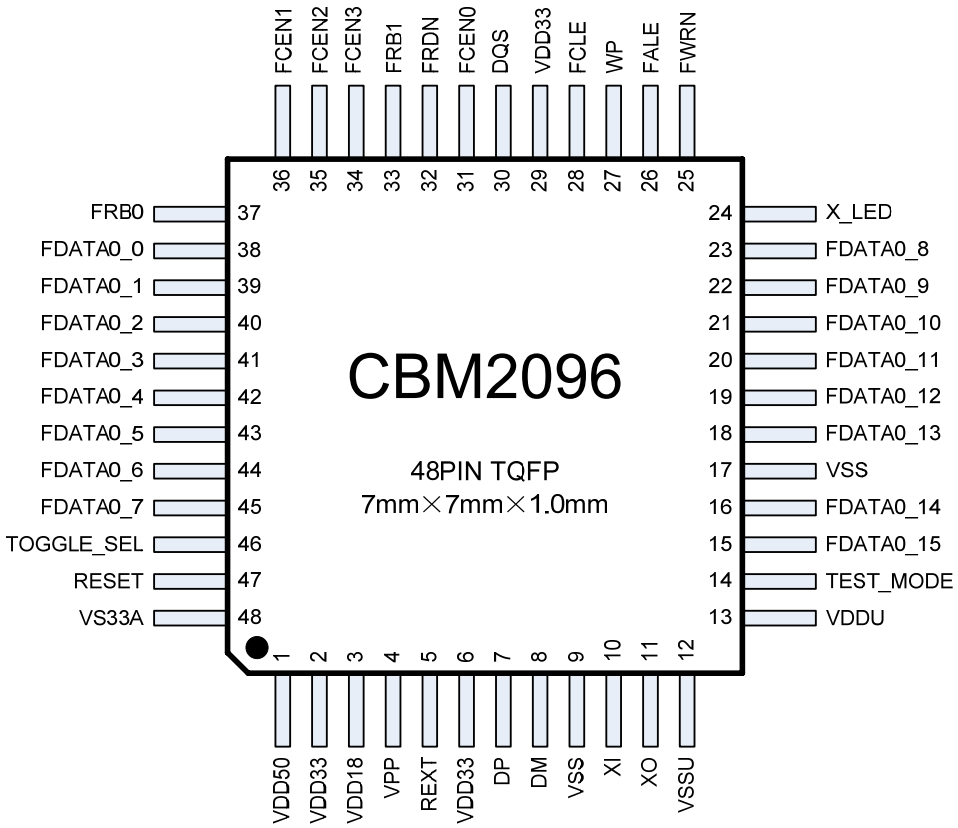
Windows, Mac and Linux compatible

3 Block Diagram



4 Pin Assignment

4.1 TQFP48 (Top Side)



5 Pin Description

Brief CBM2096 pin functions are shown in the following tables.

I: Input signal

O: Output signal

I/O: Bi-direction signal

PWR: Power signal

GND: Ground signal

PU: pull up

PD: pull down

CBM2096 TQFP48 Pin Description

TQFP48 Pin No.	Pin Name	Type	Description
1	VDD50	PWR	Regulator 5V Power Input
2	VDD33	PWR	Regulator 3.3V Power OUT
3	VDD18	PWR	Regulator 1.8V Out
4	VPP	PWR	CORE 1.8V in
5	REXT	I	Connect External Resister for current reference
6	VDD33	PWR	Padring 3.3V Power
7	DP	I/O	USB Data D+
8	DM	I/O	USB Data D-
9	VSS	GND	Padring 3.3V / Logic 1.8V Ground
10	XI	I	Connect External Capacitor
11	XO	O	Connect External Capacitor
12	VSSU	GND	Analog 1.8V Ground
13	VDDU	PWR	Analog 1.8V Power
14	TEST_MODE	I PD	Test Mode Enable Pin When high , test mode When low , normal mode
15	FDATA0_15 GPIO15	I/O PU	Group 0 Flash Data Bus - bit 15 General I/O port 15

			When select spi mode ,as spi chip select . (configure as GPIO and clear pin_64(detail in spi_ctl[13] .when select master mode , configure output , otherwise, configure as input.).
16	FDATA0_14 GPIO14	I/O PU	Group 0 Flash Data Bus - bit 14 General I/O port 14 When select spi mode, as clock out support ligh-tun sensor (configure as GPIO and clear pin_64(detail in spi_ctl[13] .when select ligh-tun mode , configure output).
17	VSS	GND	Padring 3.3V / Logic 1.8V Ground
18	FDATA0_13 GPIO13	I/O PU	Group 0 Flash Data Bus - bit 13 General I/O port 13
19	FDATA0_12 GPIO12	I/O PU	Group 0 Flash Data Bus - bit 12 General I/O port 12
20	FDATA0_11 GPIO11	I/O PU	Group 0 Flash Data Bus - bit 11 General I/O port 11
21	FDATA0_10 GPIO10	I/O PU	Group 0 Flash Data Bus - bit 10 General I/O port 10
22	FDATA0_9 GPIO9	I/O PU	Group 0 Flash Data Bus - bit 9 General I/O port 9
23	FDATA0_8 GPIO8	I/O PU	Group 0 Flash Data Bus - bit 8 General I/O port 8
24	X_LED	I/O	When TEST_MODE =1, as scan clock input. When TEST_MODE =0, as LED Indication
25	FWRN	O	Group Flash Write Enable (active low)
26	FALE	O	Group Flash Address Latch Enable
27	WP	I	Write Protect Switch Input
28	FCLE	O	Group Flash Command Latch Enable
29	VDD33	PWR	Padring 3.3V Power
30	DQS	I/O PD	DQS, only for onfi/toggle nand flash
31	FCEN0	O	Flash Chip Enable - Chip 0 (active low)
32	FRDN	O	Group Flash Read Enable (active low)
33	FRB1 /INTR	I	Group Flash Ready_Busy 1, when select flash_rb1 mode, as Group Flash Ready_Busy1 signal input(detail in soft_flag [25]). 2, when select intr mode, as external interrupt input signal(detail in soft_flag [25]).
34	/SCK(I2c) FCEN3	O	1, When select test-mode, as scan-chain output 2, When select i2c , as sck 3, When select chip select2/3 mode, as CE3 output
35	FCEN2	I/O PU	1, When select test_mode, As scan-chain input 2, when select chip select2/3 mode, as CE2 output .(active when disable test_mode)

36	X_CLK_OUT /FCEN1	I/O PU	1, When select clock input mode (1), X_CLK_OFF=1, as external input test clock. 2, When select chip select1 mode or spi master mode, as output. (only active when X_CLK_OFF =0 or de-slect spi slve mode) (1), select chip select1 mode (detail in soft_flag [28]/[25]), as CE1 output (2), otherwise, as normal clock_out ,which defined at config_r[20].
37	FRB0	I	Group Flash Ready_Busy0
38	FDATA0_0 GPIO0	I/O PU	Group 0 Flash Data Bus - bit 0 General I/O port 0
39	FDATA0_1 GPIO1	I/O PU	Group 0 Flash Data Bus - bit 1 General I/O port 1
40	FDATA0_2 GPIO2	I/O PU	Group 0 Flash Data Bus - bit 2 General I/O port 2
41	FDATA0_3 GPIO3	I/O PU	Group 0 Flash Data Bus - bit 3 General I/O port 3
42	FDATA0_4 GPIO4	I/O PU	Group 0 Flash Data Bus - bit 4 General I/O port 4
43	FDATA0_5 GPIO5	I/O PU	Group 0 Flash Data Bus - bit 5 General I/O port 5
44	FDATA0_6 GPIO6	I/O PU	Group 0 Flash Data Bus - bit 6 General I/O port 6
45	FDATA0_7 GPIO7	I/O PU	Group 0 Flash Data Bus - bit 7 General I/O port 7
46	TOGGLE_SEL	I PU	Toggle nand flash select (active low)
47	RESET	I	Reset Sign (active low)
48	VSS33A	GND	Analog 3.3V Ground

6 Electrical Characteristics

6.1 Absolute maximum ratings

In accordance with the Absolute Maximum Rating System (IEC 60134).

symbol	parameter	conditions		min	max	unit
VDD33	analog supply voltage			-0.5	5.5	v
VDD18	digital supply voltage			-0.5	4.5	v
VDD50	input voltage			-0.5	5.5	v
Vesd	electrostatic discharge voltage[1]	ILI < 1 A	DP, DM and GND pins	-4000	+4000	v
			other pins	-2000	+2000	
Tstg	storage temperature			-40	+125	℃

[1] Equivalent to discharging a 100 pF capacitor via a 1.5 k resistor (Human Body Model).

6.2 Recommended operating conditions

symbol	Parameter	conditions	min	Typ	max	Unit
VDD33	analog supply voltage		3.0	3.3	3.6	V
VDD18	digital supply voltage		1.62	1.8	1.98	V
VDD50	input voltage		4.5	5	5.5	V
VI(AI/O)	input voltage on analog I/O pins DP DM	Low/Full speed	0	3.3	3.6	V
		High speed	0	400	-	mV
Tamb	ambient temperature		0	-	+70	℃

6.3 Static characteristics

All parameters are measured at VCCA = VCCD = 3.0 to 3.6 V; VAGND = VDGND = 0 V;
Tamb = -40 to 85 ℃;

symbol	Parameter	Conditions	min	Typ	max	Unit
ICC	operating supply current	Full-speed transmitting and receiving;	-	29.5	-	mA
		high-speed transmitting and receiving	-	60		
ICC(susp)	suspend supply current	in suspend mode	-	4		mA

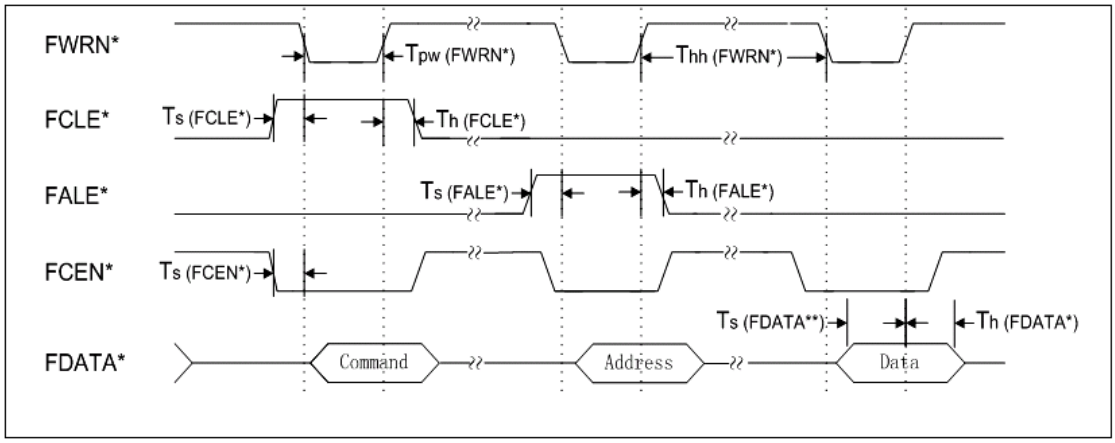
6.4 Dynamic characteristics

6.4.1 Normal NAND FLASH Dynamic characteristics

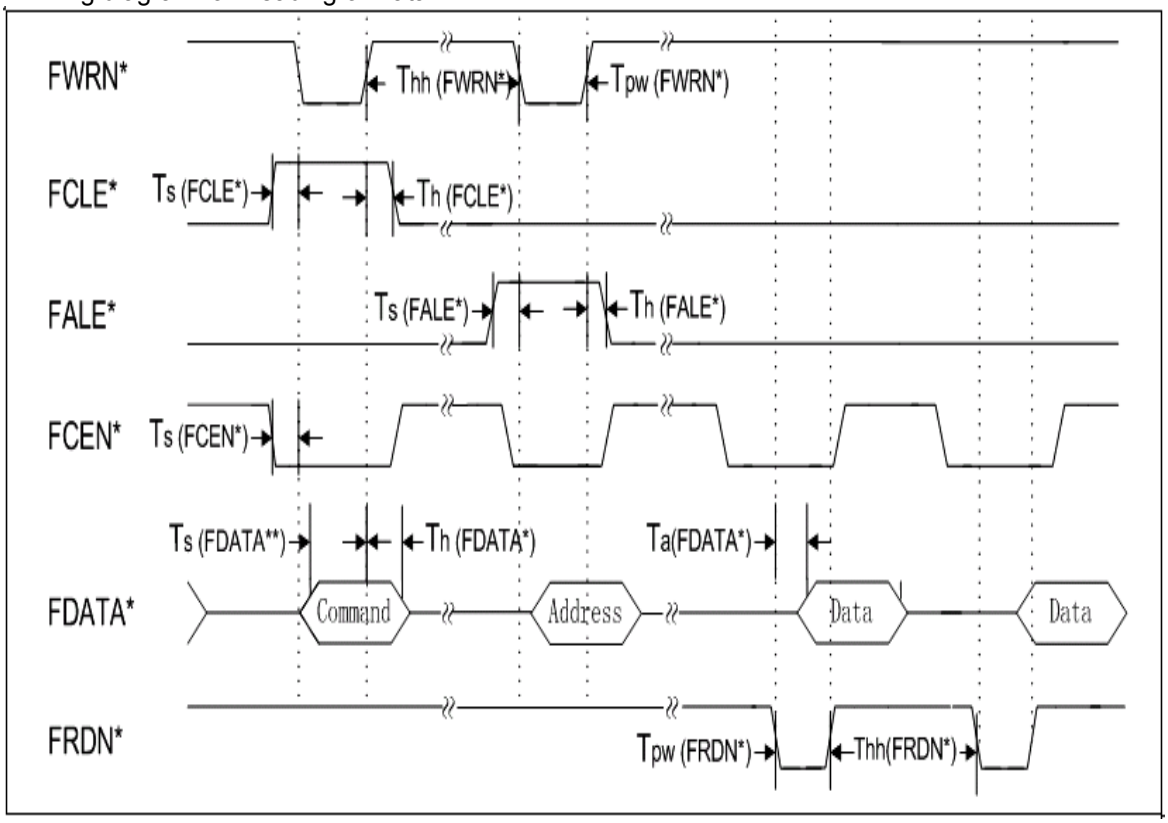
All parameters are measured at VCCA = VCCD = 3.0 to 3.6 V; VAGND = VDGND = 0 V;
Tamb = -40 to 85 ℃ ;

symbol	Parameter	conditions	min	Typ	max	Unit
Ts(FDATA*)	FDATA* setup time relative to rising FWRN* edge	Configured by firmware	8	33	75	ns
Th(FDATA*)	FDATA* hold time relative to falling FWRN* edge	Configured by firmware	8	33	75	ns
Ts (FCLE*)	FCLE* setup time relative to falling FWRN* edge	Configured by firmware	8	16	25	ns
Th (FCLE*)	FCLE* hold time relative to rising FWRN* edge	Configured by firmware	10	16	75	ns
Ts (FALE*)	FALE* setup time relative to falling FWRN* edge	Configured by firmware	8	16	25	ns
Th (FALE*)	FALE* hold time relative to rising FWRN* edge	Configured by firmware	10	16	75	ns
Ts (FCEN*)	FCEN* setup time relative to falling FWRN* edge	Configured by firmware	-	99		ns
Tpw (FWRN*)	FWRN* Pulse Width	Configured by firmware	8	33	75	ns
Thh (FWRN*)	FWRN* high hold time	Configured by firmware	8	33	75	ns
Ta(FDATA*)	FDATA* access time relative to falling FRDN* edge		-5	0	5	ns
Tpw (FRDN*)	FWRN* Pulse Width	Configured by firmware	8	33	75	ns
Thh (FRDN*)	FWRN* high hold time	Configured by firmware	8	33	75	ns

Timing diagram for Writing of Data



Timing diagram for Reading of Data



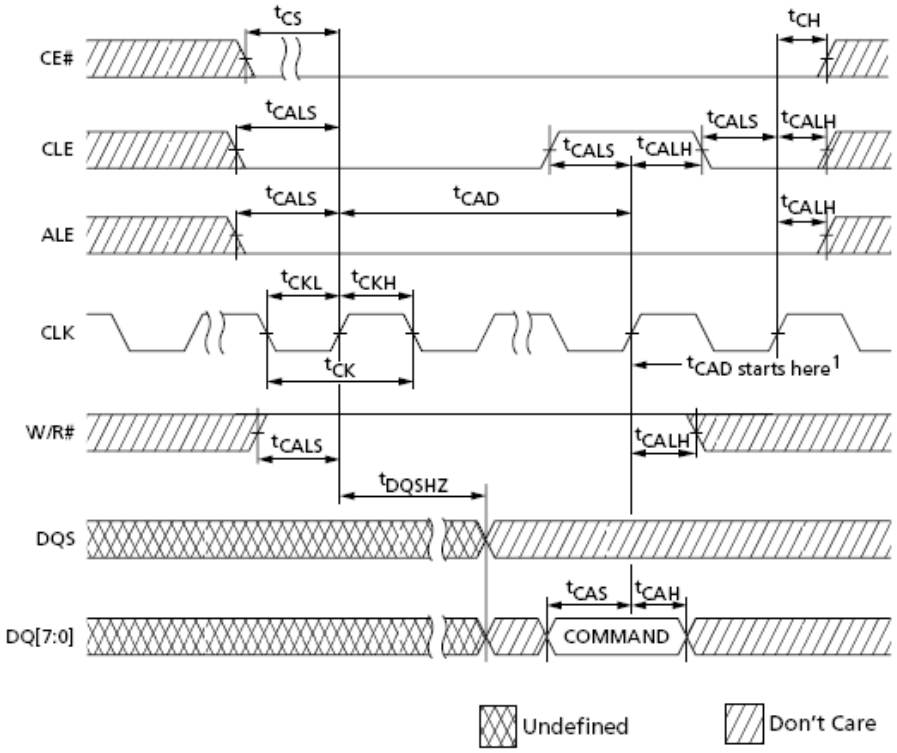
6.4.2 ONFI NAND FLASH Dynamic characteristics

CBM2096 only support Mode0/Mode1/Mode2.

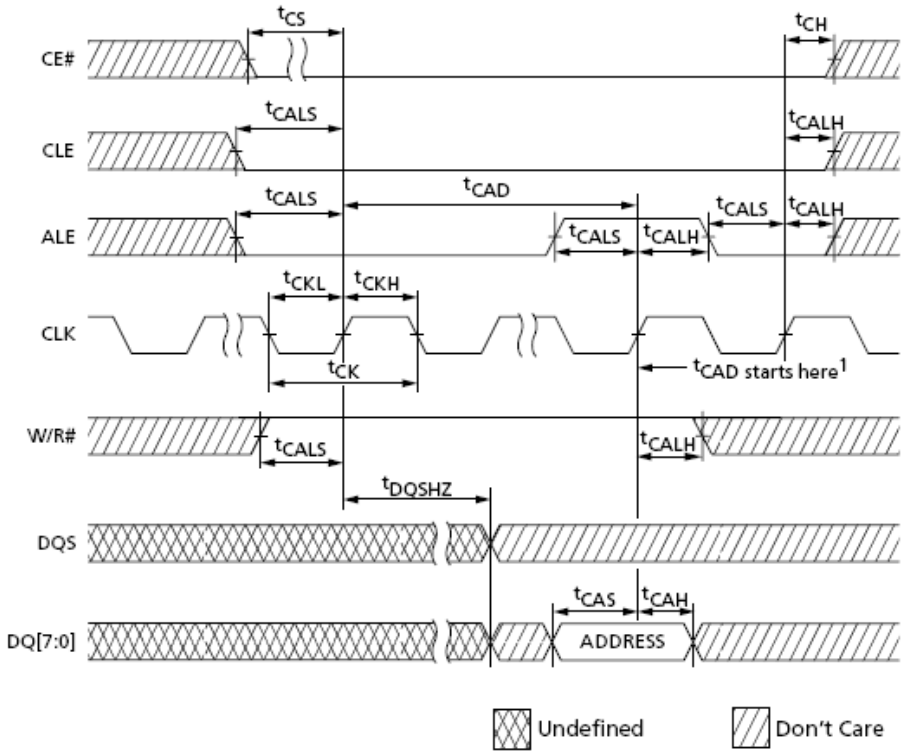
Parameter	Symbol	Mode 0		Mode 1		Mode 2		Mode 3		Mode 4		Unit	Notes
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
Clock Period		50		30		20		15		12		ns	–
Frequency		≈20		≈33		≈50		≈67		≈83		MHz	–
Access window of DQ[7:0] from CLK	^{t}AC	–	20	–	20	–	20	–	20	–	20	ns	–
ALE to data loading time	^{t}ADL	100	–	100	–	70	–	70	–	70	–	ns	–
Cmd, Addr, Data delay	^{t}CAD	25	–	25	–	25	–	25	–	25	–	ns	1
ALE, CLE, W/R# hold	^{t}CALH	10	–	5	–	4	–	3	–	2.5	–	ns	–
ALE, CLE, W/R# setup	^{t}CALS	10	–	5	–	4	–	3	–	2.5	–	ns	–
DQ hold - Cmd, Addr	^{t}CAH	10	–	5	–	4	–	3	–	2.5	–	ns	–
DQ setup - Cmd, Addr	^{t}CAS	10	–	5	–	4	–	3	–	2.5	–	ns	–
Change column setup to data in/out or next command	^{t}CCS	200	–	200	–	200	–	200	–	200	–	ns	2
CE# hold	^{t}CH	10	–	5	–	4	–	3	–	2.5	2	ns	–
Average CLK cycle time	^{t}CK (avg)	50	100	30	50	20	30	15	20	12	15	ns	3
Absolute CLK cycle time, from rising edge to rising edge	^{t}CK (abs)	^{t}CK(abs) MIN = ^{t}CK(avg) + ^{t}JIT(per) MIN ^{t}CK(abs) MAX = ^{t}CK (avg) + ^{t}JIT(per) MAX										ns	–
CLK cycle HIGH	^{t}CKH (abs)	0.43	0.57	0.43	0.57	0.43	0.57	0.43	0.57	0.43	0.57	^{t}CK	4
CLK cycle LOW	^{t}CKL (abs)	0.43	0.57	0.43	0.57	0.43	0.57	0.43	0.57	0.43	0.57	^{t}CK	4
Data output end to W/R# HIGH	^{t}CKWR	^{t}CKWR(MIN) = RoundUp[^{t}DQSCK(MAX) + ^{t}CK) / ^{t}CK]										^{t}CK	–
CE# setup	^{t}CS	35	–	25	–	15	–	15	–	15	–	ns	–
Data In hold	^{t}DH	5	–	2.5	–	1.7	–	1.3	–	1.1	–	ns	–
Access window of DQS from CLK	^{t}DQSCK	–	20	–	20	–	20	–	20	–	20	ns	–
DQS, DQ[7:0] Driven by NAND	^{t}DQSD	0	20	0	20	0	20	0	20	0	20	ns	–
DQS, DQ[7:0] to tri-state	^{t}DQSHZ	–	20	–	20	–	20	–	20	–	20	ns	5
DQS input high pulse width	^{t}DQSH	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	^{t}CK	–
DQS input low pulse width	^{t}DQSL	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	^{t}CK	–
DQS-DQ skew	^{t}DQSQ	–	5	–	2.5	–	1.7	–	1.3	–	1.1	ns	–
Data input	^{t}DQSS	0.75	1.25	0.75	1.25	0.75	1.25	0.75	1.25	0.75	1.25	^{t}CK	–
Data In setup	^{t}DS	5	–	3	–	2	–	1.5	–	1.1	–	ns	–

Parameter	Symbol	Mode 0		Mode 1		Mode 2		Mode 3		Mode 4		Unit	Notes
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
DQS falling edge from CLK rising - hold	^{t}DSH	0.2	–	0.2	–	0.2	–	0.2	–	0.2	–	^{t}CK	–
DQS falling to CLK rising - setup	^{t}DSS	0.2	–	0.2	–	0.2	–	0.2	–	0.2	–	^{t}CK	–
Data Valid Window	^{t}DVW	^{t}DVW = ^{t}QH - ^{t}DQSQ										ns	–
Half Clock Period	^{t}HP	^{t}HP = Min(^{t}CKH, ^{t}CKL)										ns	–
The deviation of a given ^{t}CK(abs) from ^{t}CK (avg)	^{t}JIT(per)	-0.7	0.7	-0.7	0.7	-0.7	0.7	-0.6	0.6	-0.6	0.6	ns	–
DQ-DQS hold, DQS to first DQ to go non-valid, per access	^{t}QH	^{t}QH = ^{t}HP - ^{t}QHS										ns	–
Data Hold Skew Factor	^{t}QHS	–	6	–	3	–	2	–	1.5	–	1.2	ns	–
Data output to command, address, or data input	^{t}RHW	100	–	100	–	100	–	100	–	100	–	ns	–
Ready to data output	^{t}RR	20	–	20	–	20	–	20	–	20	–	ns	–
Device reset time (Read/Program/Erase)	^{t}RST	–	5/10/500	–	5/10/500	–	5/10/500	–	5/10/500	–	5/10/500	µs	6
CLK high to R/B# low	^{t}WB	–	100	–	100	–	100	–	100	–	100	ns	–
Command cycle to data output	^{t}WHR	80	–	60	–	60	–	60	–	60	–	ns	–
DQS write preamble	^{t}WPRE	1.5	–	1.5	–	1.5	–	1.5	–	1.5	–	^{t}CK	–
DQS write postamble	^{t}WPST	1.5	–	1.5	–	1.5	–	1.5	–	1.5	–	^{t}CK	–
W/R# LOW to data output cycle	^{t}WRCK	20	–	20	–	20	–	20	–	20	–	ns	–
WP# transition to command cycle	^{t}WW	100	–	100	–	100	–	100	–	100	–	ns	–

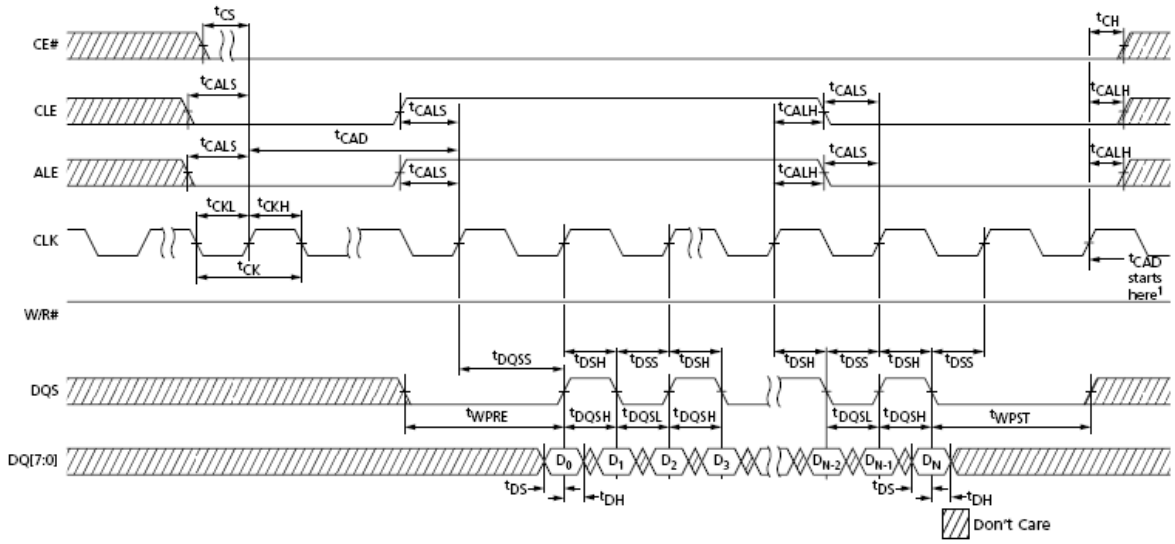
Notes:
1. Delay is from start of command to next command, address, or data cycle; start of address to next command, address, or data cycle; and end of data to start of next command, address, or data cycle.
2. This value is specified in the parameter page.
3. ^{t}CK(avg) is the average clock period over any consecutive 200-cycle window.
4. ^{t}CKH(abs) and ^{t}CKL(abs) include static offset and duty cycle jitter.
5. ^{t}DQSHZ begins when W/R# is latched HIGH by CLK. This parameter is not referenced to a specific voltage level; it specifies when the device outputs are no longer driving.
6. If RESET (FFh) is issued when the target is idle, the target goes busy for a maximum of 5µs.



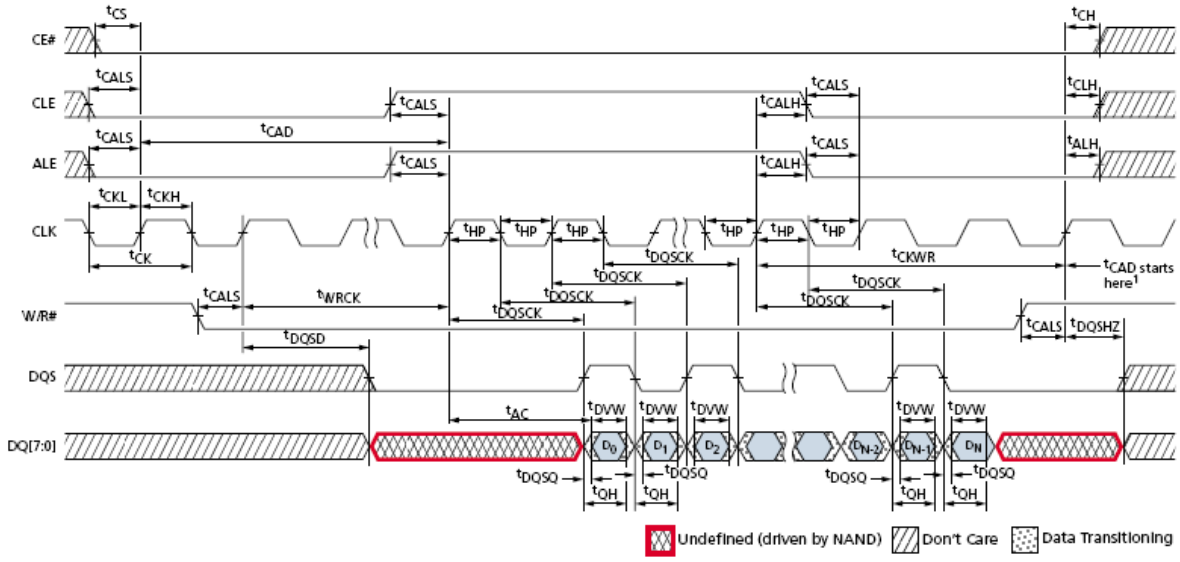
Notes: 1. When CE# remains LOW, tCAD begins at the rising edge of the clock from which the command cycle is latched for subsequent command, address, data input, or data output cycle(s).



Notes: 1. When CE# remains LOW, tCAD begins at the rising edge of the clock from which the command cycle is latched for subsequent command, address, data input, or data output cycle(s).



Notes:
1. When CE# remains LOW, tCAD begins at the first rising edge of the clock after tWPST completes.
2. tDSH (MIN) generally occurs during tDQSS (MIN).
3. tDSS (MIN) generally occurs during tDQSS (MAX).



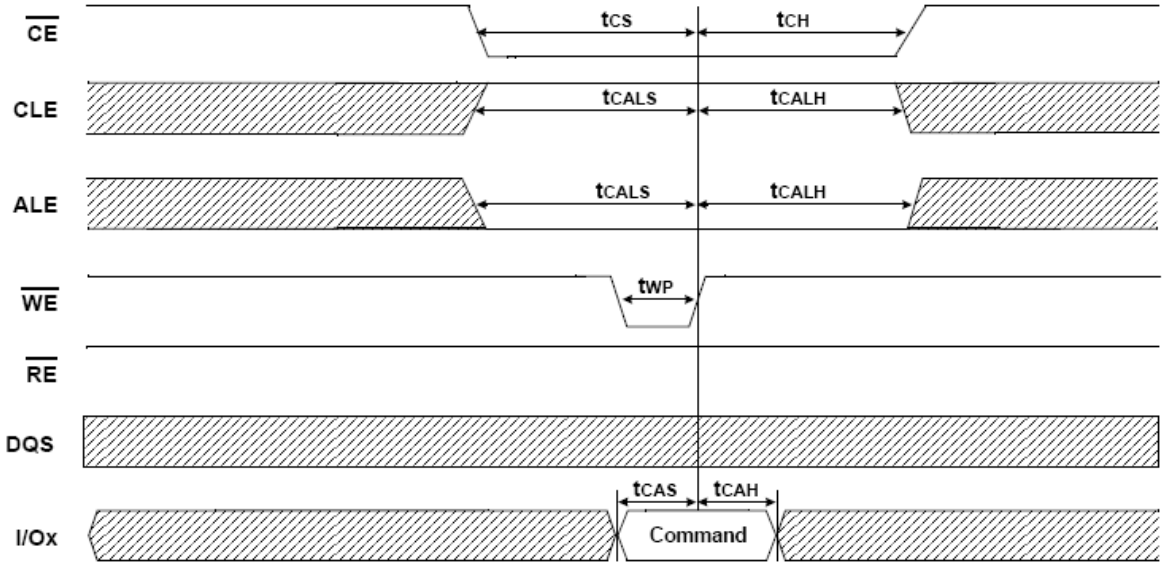
Notes:
1. When CE# remains LOW, tCAD begins at the rising edge of the clock after tCKWR for subsequent command or data output cycle(s).
2. See Figure 25 on page 33 for details of W/R# behavior.
3. tAC is the DQ output window relative to CLK and is the long-term component of DQ skew.
4. For W/R# transitioning HIGH: DQ[7:0] and DQS go to tri-state.
5. For W/R# transitioning LOW: DQ[7:0] drives current state and DQS goes LOW.
6. After final data output, DQ[7:0] is driven until W/R# goes HIGH, but is not valid.

6.4.3 TOGGLE NAND FLASH Dynamic characteristics

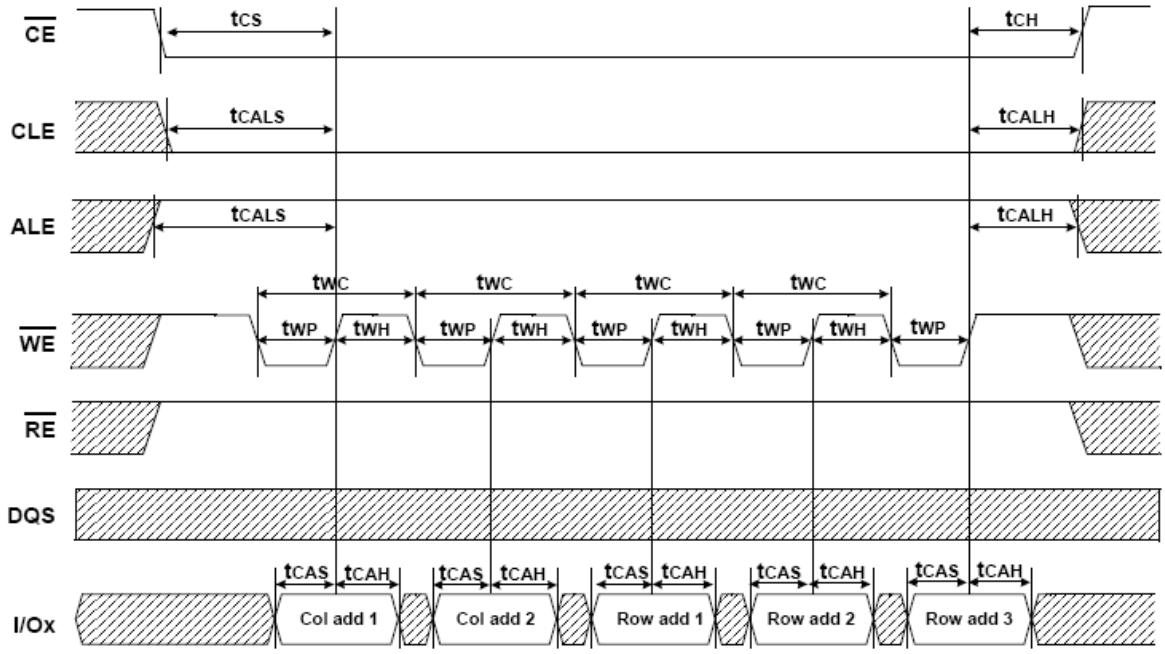
CBM2096 only support 66Mbps/80Mbps.

Parameter	Sym-bol	66Mbps		80Mbps		133Mbps		Unit
		Min	Max	Min	Max	Min	Max	
CLE/ALE Setup Time	t_{CALS}	15	-	15	-	15	-	ns
CLE/ALE Hold Time	t_{CALH}	5	-	5	-	5	-	ns
DQS Setup Time for data input start	t_{CDQSS}	100	-	100	-	100	-	ns
DQS Hold Time for data input finish	t_{CDQSH}	100	-	100	-	100	-	ns
Command Write cycle to Address Write cycle Time for Random data input	t_{CWAW}	300	-	300	-	300	-	ns
$\overline{CE}$ Setup Time	t_{CS}	20	-	20	-	20	-	ns
$\overline{CE}$ Hold Time	t_{CH}	5	-	5	-	5	-	ns
Command/Address Setup Time	t_{CAS}	5	-	5	-	5	-	ns
Command/Address Hold Time	t_{CAH}	5	-	5	-	5	-	ns
Data Setup Time	t_{DS}	4	-	3.3	-	2.0	-	ns
Data Hold Time	t_{DH}	3.6	-	3	-	1.8	-	ns
Write Cycle Time	t_{WC}	25	-	25	-	25	-	ns
$\overline{WE}$ High pulse width	t_{WH}	11	-	11	-	11	-	ns
$\overline{WE}$ Low pulse Width	t_{WP}	11	-	11	-	11	-	ns
Address to Data Loading Time	t_{ADL}	300	-	300	-	300	-	ns
Data Transfer from Cell to Register	t_R	-	100	-	100	-	100	µs
Ready to $\overline{RE}$ High	t_{RR}	20	-	20	-	20	-	ns
$\overline{CE}$ Low to $\overline{RE}$ Low	t_{CR}	10	-	10	-	10	-	ns
ALE Low to $\overline{RE}$ Low	t_{AR}	10	-	10	-	10	-	ns
CLE to $\overline{RE}$ Low	t_{CLR}	10	-	10	-	10	-	ns
$\overline{WE}$ High to Busy	t_{WB}	-	100	-	100	-	100	ns
Read Cycle Time	t_{RC}	30	-	25	-	15	-	ns
$\overline{RE}$ High pulse width	t_{REH}	13	-	11	-	6.5	-	ns
$\overline{RE}$ Low pulse width	t_{RP}	13	-	11	-	6.5		ns
$\overline{CE}$ High to Output Hi-Z	t_{CHZ}	-	30	-	30	-	30	ns
CLE High to Output Hi-Z	t_{CLHZ}	-	30	-	30	-	30	ns
Data Strobe Cycle Time	t_{DSC}	30	-	25	-	15	-	ns
DQS Input Low Pulse Width	t_{DQSL}	13	-	11	-	6.5	-	ns
DQS Input High Pulse Width	t_{DQSH}	13	-	11	-	6.5	-	ns
$\overline{WE}$ High to $\overline{RE}$ Low	t_{WHR}	120	-	120	-	120	-	ns
$\overline{WE}$ High to $\overline{RE}$ Low for Random data out	t_{WHR2}	300	-	300	-	300	-	ns

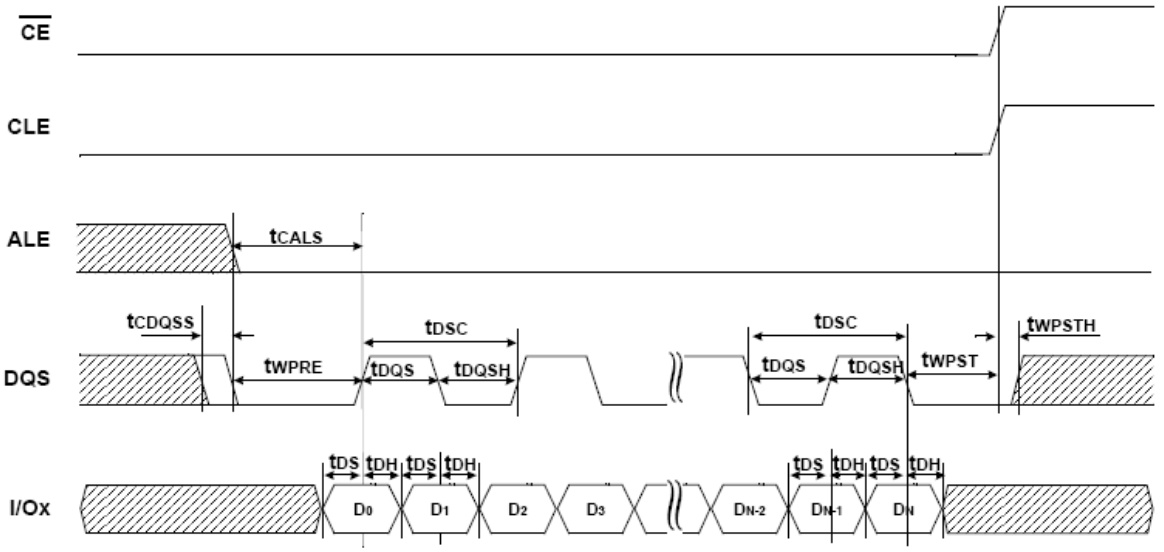
$\overline{RE}$ to DQS and DQ delay	tDQSRE	-	25	-	25	-	25	ns
Read Preamble	tRPRE	15	-	15	-	15	-	ns
Read Postamble	tRPST	tDQSRE+0.5xtRC	-	tDQSRE+0.5xtRC	-	tDQSRE+0.5xtRC	-	ns
Read Postamble Hold Time	tRPSTH	5		5		5	-	ns
Write Preamble	tWPRE	15		15		15	-	ns
Write Postamble	tWPST	6.5		6.5		6.5	-	ns
Write Postamble Hold Time	tWPSTH	5		5		5	-	ns
Output skew among data output and corresponding DQS	tDQSQ	-	2.5	-	2	-	1.4	ns
DQS hold skew factor	tQHS	-	2.5	-	2	-	1.4	ns
Output hold time from DQS	tQH	tQH = tREH/tRP - tQHS						ns
Output data valid window	tDVW	tDVW = tQH - tDQSQ						ns
Device Resetting Time (Read/Program/Erase)	tRST(1)	10/30/100						µs



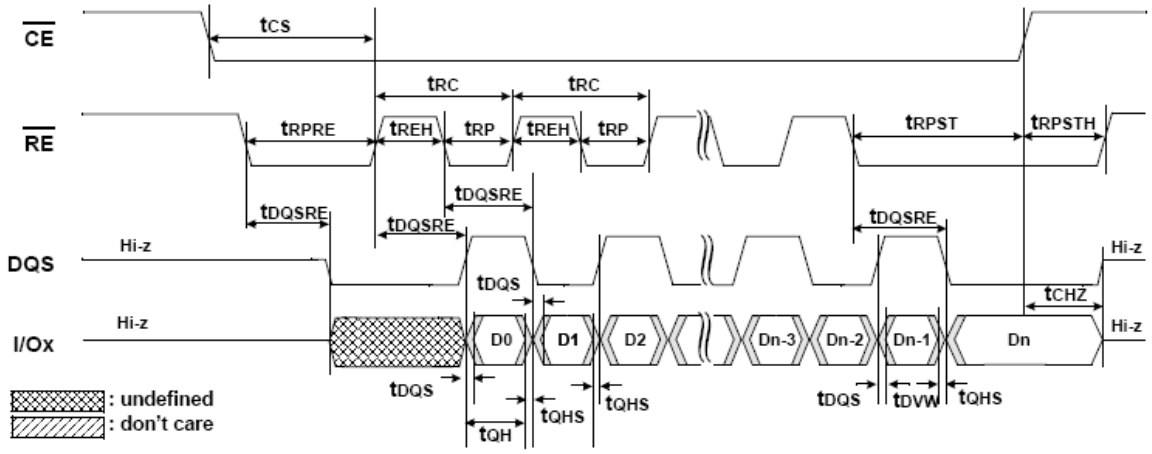
NOTE :
1. Command information is lached by $\overline{WE}$ going high, when $\overline{CE}$ is Low, CLE is High, and ALE is Low.
2. DQS should be set to 'Low' when these commands(85h, 10h, 11h) is input.



NOTE :
Row address consists of page address and block address.



NOTE :
1) Data-input condition should be satisfied before DQS toggling for data input; data-input condition is that $\overline{CE}$ & CLE & ALE are low and $\overline{RE}$ & $\overline{WE}$ are high
2) DQS should be either high or low before data-input condition is set.
3) Data-input condition should be kept during DQS toggling for data input including pre-amble and post-amble time.
4) Becase using toggle DDR interface, an even number of bytes should be always transferred when both data input and data output

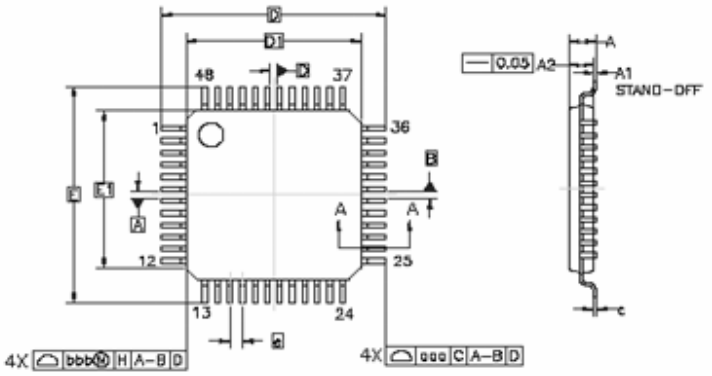


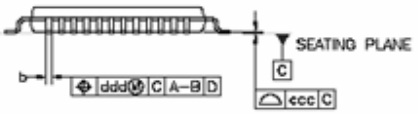
NOTE :
1) Data-output condition should be satisfied before $\overline{RE}$ toggling for data output; data-output condition is that $\overline{CE}$ & CLE & ALE are low and $\overline{WE}$ is high
2) $\overline{RE}$ should be either high or low before data-output condition is set.
3) Data-output condition should be kept during $\overline{RE}$ toggling for data output including pre-amble and post-amble time.
4) DQS and Data out buffers are turned on when $\overline{RE}$ is low for pre-amble operation under data-out condition
5) DQS and Data out buffers turn from valid value to high-z if either $\overline{CE}$ or CLE goes High.
6) an even number of bytes should be always transferred when both data input and data output

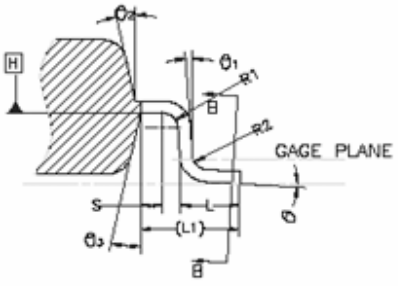
7 Mechanical Dimensions

7.1 48-Pin CBM2096 Package Outline Dimension

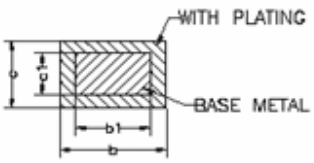
DOC No.: 0048-TQ7.0X7.0-01-A







SECTION A-A



SECTION B-B

ALL DIMENSIONS ARE IN MILLIMETERS.

SYMBOL	MILLIMETER			INCH		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	—	—	1.20	—	—	0.047
A1	0.05	—	0.15	0.002	—	0.006
A2	0.95	1.00	1.05	0.037	0.039	0.041
D	9.00 BASIC			0.354 BASIC		
D1	7.00 BASIC			0.276 BASIC		
E	9.00 BASIC			0.354 BASIC		
E1	7.00 BASIC			0.276 BASIC		
R2	0.08	—	0.20	0.003	—	0.008
R1	0.08	—	—	0.003	—	—
θ	0°	3.5°	7°	0°	3.5°	7°
θ1	0°	—	—	0°	—	—
θ2	11°	12°	13°	11°	12°	13°
θ3	11°	12°	13°	11°	12°	13°
c	0.09	—	0.20	0.004	—	0.008
c1	0.09	0.127	0.16	0.004	0.005	0.006
L1	1.00 REF			0.039 REF		
L	0.45	0.60	0.75	0.018	0.024	0.030
S	0.20	—	—	0.008	—	—
b	0.17	0.22	0.27	0.007	0.009	0.011
b1	0.17	0.20	0.23	0.007	0.008	0.009
e	0.50 BSC.			0.020 BSC.		
eee	0.20			0.008		
bbb	0.20			0.008		
ccc	0.08			0.003		
ddd	0.07			0.003		

NOTES :

1. DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 mm PER SIDE. DIMENSION D1 AND E1 DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE H;
3. DIMENSION b DOES NOT INUDE DAMBER PROTRUSION. ALLOWABLE DAMBER PROTRUSION SHALL BE 0.08mm TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONTION. DAMBER CANNOT BE LOCATED ON THE LOWER RADIUS OR THE LEAD FOOT;
4. DIMENSION A INCLUDES STANDOFF HEIGHT A1,PACKAGE BODY THICKNESS AND UD HEIGHT, BUT DOES NOT INCLUDE ATTACHED FEATURES;
5. PARALLELISM MEASUREMENT SHALL EXCLUDE ANY EFFECT OF MARK ON TOP SURFACE OF PACKAGE.

TQFP 7.0 × 7.0 mm 48L Package Outline Dimension

8 Copyright Notice

Right to make changes —Shenzhen Chipsbank Technologies Co.,Ltd. reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. The information contained in this manual is provided for the general use by our customers. Our customers should be aware that the personal computer field is the subject of many patents. Our customers should ensure that they take appropriate action so that their use of our products does not infringe upon any patents. It is the policy of Shenzhen Chipsbank Technologies Co.,Ltd. to respect the valid patent rights of third parties and not to infringe upon or assist others to infringe upon such rights.